

isc N-Channel MOSFET Transistor

IPW50R250CP

• FEATURES

- Static drain-source on-resistance: R_{DS}(on)≤250mΩ
- Enhancement mode:
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation





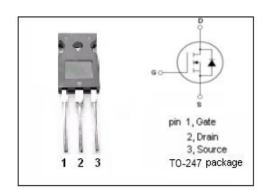
High Peak Current Capability

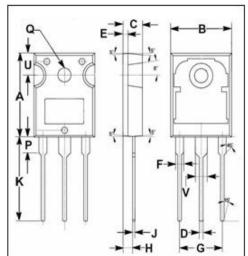
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|-------------------|-------------------------------------|---------|---------------|
| $V_{	extsf{DSS}}$ | Drain-Source Voltage | 500 | V |
| V _{GS} | Gate-Source Voltage | ±20 | V |
| I _D | Drain Current-Continuous | 13 | А |
| I _{DM} | Drain Current-Single Pulsed | 31 | А |
| P _D | Total Dissipation @Tc=25°C | 114 | W |
| Tj | Max. Operating Junction Temperature | 150 | $^{\circ}$ C |
| T _{stg} | Storage Temperature | -55~150 | ${\mathbb C}$ |

• THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT | |
|----------|---------------------------------------|-----|------|--|
| Rth(j-c) | Channel-to-case thermal resistance | 1.1 | °C/W | |
| Rth(j-a) | Channel-to-ambient thermal resistance | 62 | °C/W | |





| 9 | mm | | | |
|-----|-------|-------|--|--|
| DIM | MIN | MAX | | |
| Α | 19.80 | 20.20 | | |
| В | 15.40 | 15.80 | | |
| C | 4.90 | 5.10 | | |
| D | 0.90 | 1.10 | | |
| E | 1.40 | 1.60 | | |
| F | 1.90 | 2.10 | | |
| G | 10.80 | 11.00 | | |
| Н | 2.40 | 2.60 | | |
| J | 0.50 | 0.70 | | |
| K | 19.50 | 20.50 | | |
| P | 3.90 | 4.10 | | |
| Q | 3.30 | 3.50 | | |
| U | 5.20 | 5.40 | | |
| V | 2.90 | 3.10 | | |



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | ТҮР | MAX | UNIT |
|----------------------|--------------------------------|--|-----|-----|------|------|
| BV _{DSS} | Drain-Source Breakdown Voltage | V _{GS} =0V; I _D =250 μ A | 500 | | | V |
| V _{GS} (th) | Gate Threshold Voltage | VDS=VGS; I _D =520 μ A | 2.5 | | 3.5 | V |
| R _{DS(on)} | Drain-Source On-Resistance | V _{GS} =10V; I _D =7.8A | | | 0.25 | Ω |
| l _{GSS} | Gate-Source Leakage Current | V _{GS} = 20V; V _{DS} = 0V | | | 0.1 | μА |
| I _{DSS} | Drain-Source Leakage Current | V _{DS} =500V; V _{GS} = 0V | | | 1 | μА |
| V _{SD} | Diode forward voltage | I _F =7.8A, V _{GS} = 0V | | | 1.2 | V |

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